

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	100	V
Gate-Source Voltage			V <sub>GSS</sub>	±16	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	(Note 6)	T <sub>A</sub> = +25°C	I <sub>D</sub>	1.6	A
		T <sub>A</sub> = +70°C		1.3	
	(Note 5)	T <sub>A</sub> = +25°C	I <sub>D</sub>	1.4	A
		T <sub>A</sub> = +70°C		1.1	
Maximum Continuous Body Diode Forward Current (Note 6)			I <sub>S</sub>	0.6	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	8	A

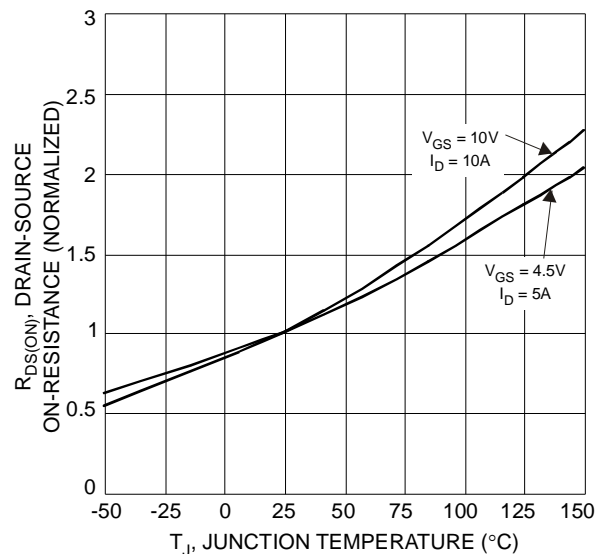
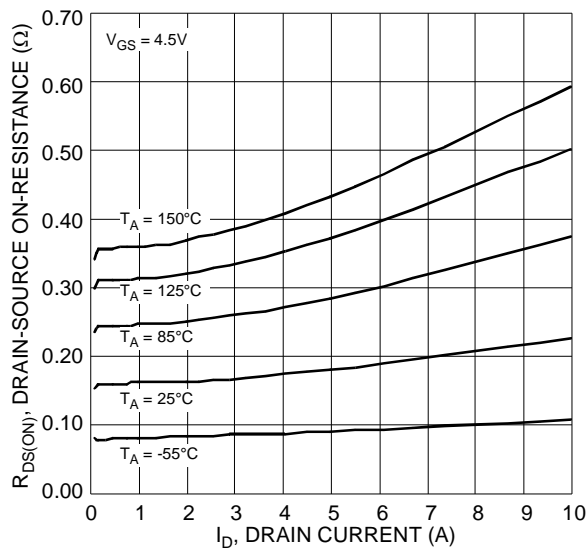
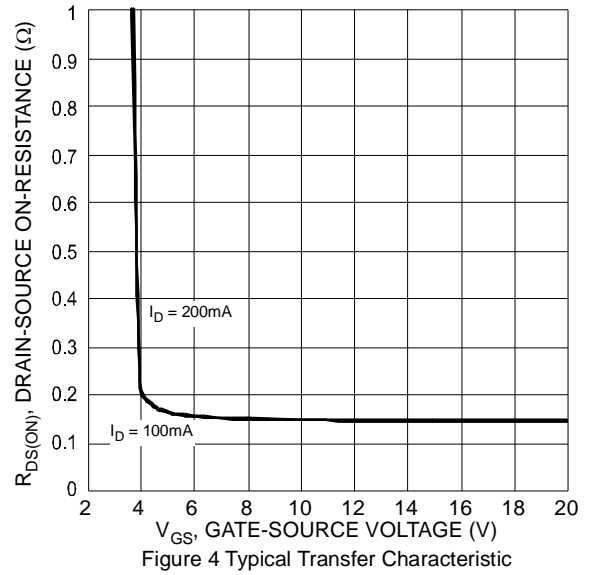
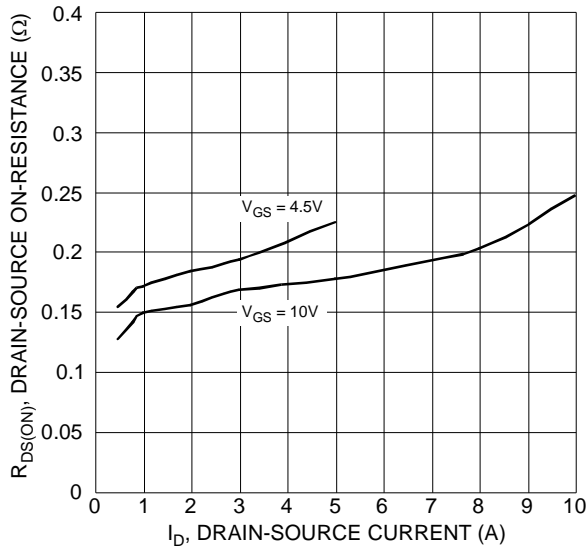
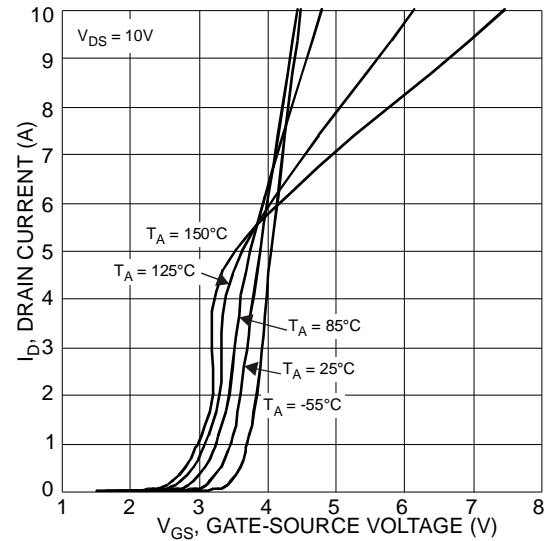
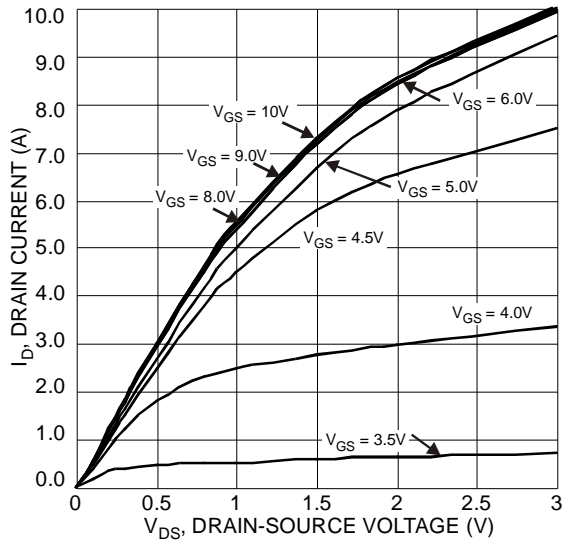
**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

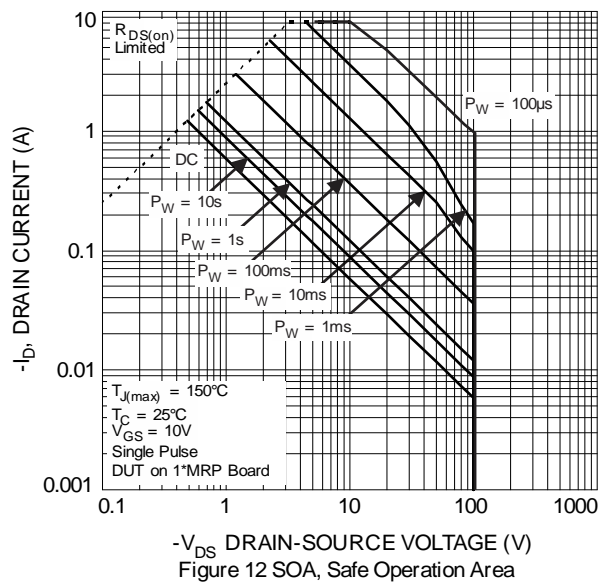
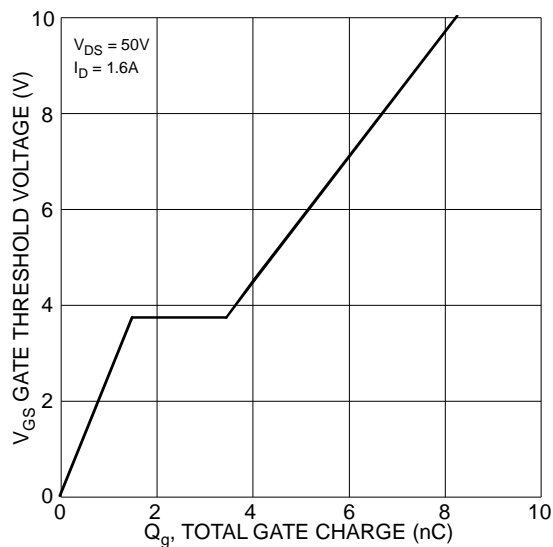
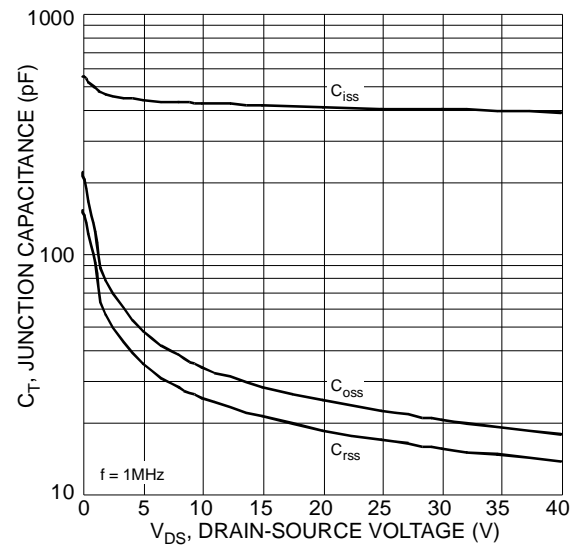
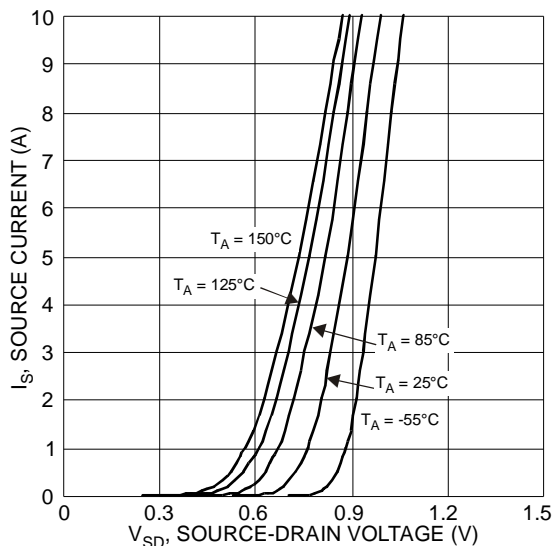
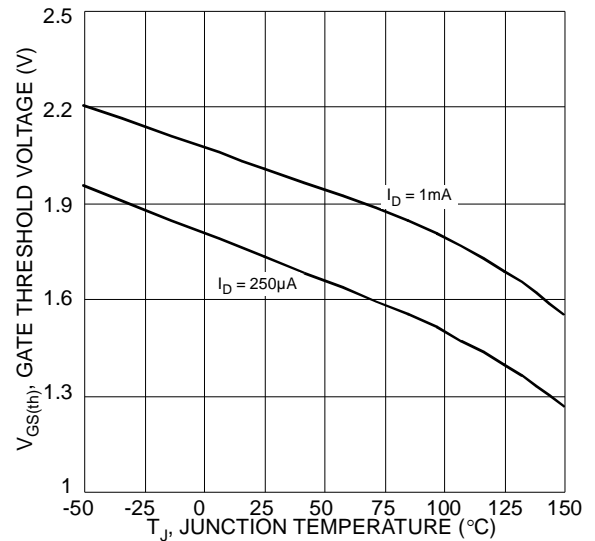
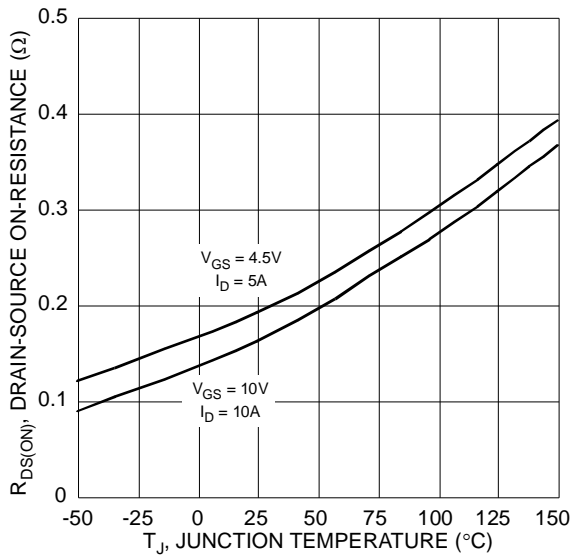
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.3	W
	T <sub>A</sub> = +70°C		0.8	
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>θJA</sub>	94	°C/W
	(Note 5)		177	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

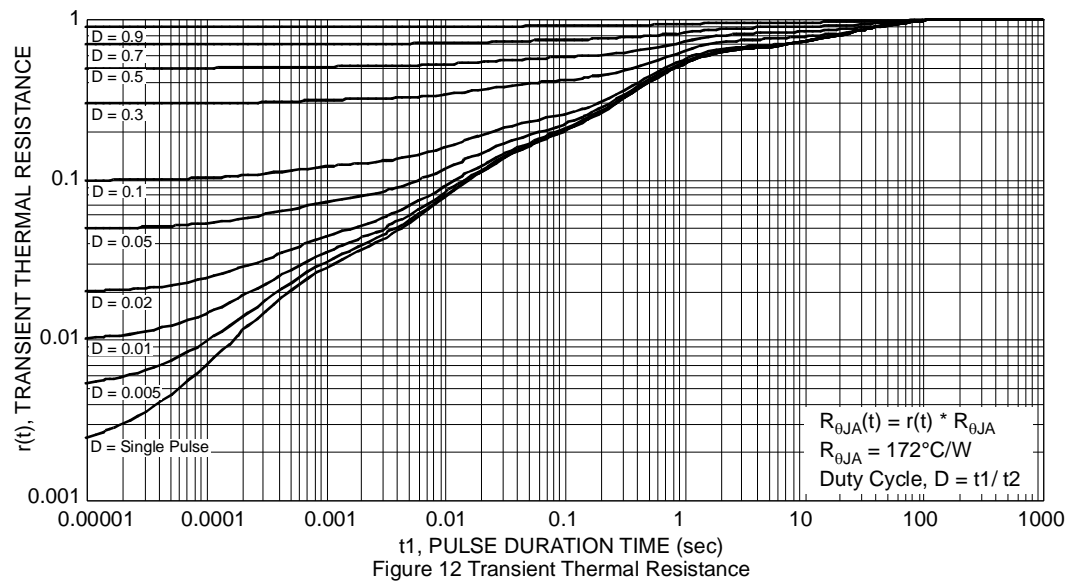
**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	—	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	—	220	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 1.6A
			—	250		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 1.3A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	401	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	22	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	17	—		
Gate Resistance	R <sub>g</sub>	—	2.1	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	4.1	—	nC	V <sub>DS</sub> = 50V, I <sub>D</sub> = 1.6A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	8.3	—		
Gate-Source Charge	Q <sub>gs</sub>	—	1.5	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	6.8	—	ns	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 4.5V, R <sub>G</sub> = 6.8Ω, I <sub>D</sub> = 1A
Turn-On Rise Time	t <sub>r</sub>	—	8.2	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	7.9	—		
Turn-Off Fall Time	t <sub>f</sub>	—	3.6	—		
Reverse Recovery Time	t <sub>rr</sub>	—	17	—	ns	I <sub>F</sub> = 1.1A, di/dt = 100A/μs
Reverse Recovery Charge	Q <sub>rr</sub>	—	9.8	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.



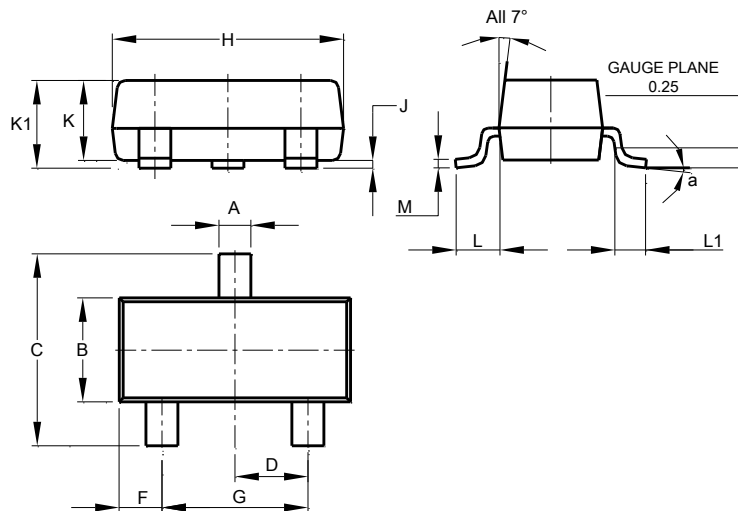




## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT23

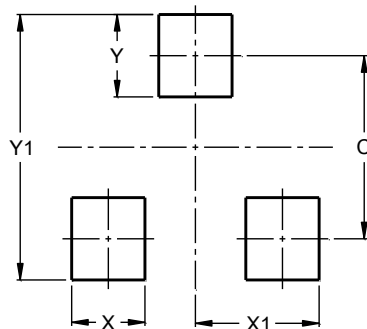


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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